

isc N-Channel MOSFET Transistor

IPP50R500CE

• FEATURES

- With low gate drive requirements
- Very high commutation ruggedness
- Extremely high frequency operation
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• APPLICATIONS

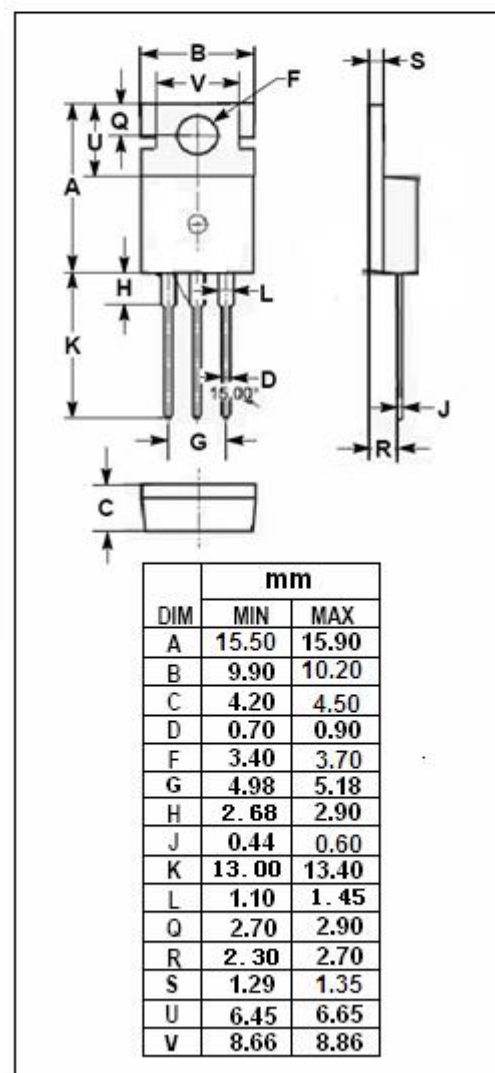
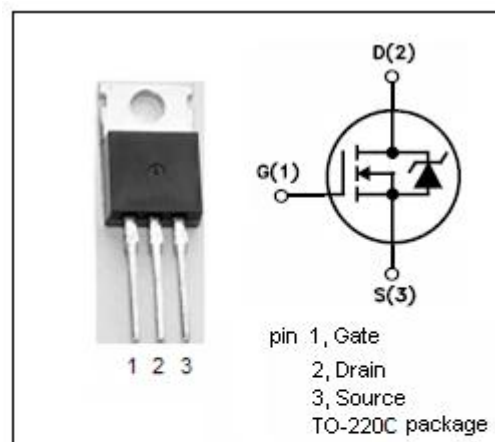
- Switching applications
- LCD&PDP TV
- PC silverbox
- UPS and solar

• ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DS}	Drain-Source Voltage	500	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-Continuous@ $T_c=25^{\circ}\text{C}$ $T_c=100^{\circ}\text{C}$	11.1 7	A
I_{DM}	Drain Current-Single Pulsed	24	A
P_D	Total Dissipation	81	W
T_j	Operating Junction Temperature	-55~150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~150	$^{\circ}\text{C}$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	1.55	$^{\circ}\text{C/W}$
$R_{th(ch-a)}$	Channel-to-ambient thermal resistance	62	$^{\circ}\text{C/W}$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DS}	Drain-Source Breakdown Voltage	$V_{GS}=0V; I_D=0.25mA$	500			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=\pm 20V; I_D=1.4mA$	2.5		3.5	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V; I_D=2.3A$		450	500	$m\Omega$
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V; V_{DS}=0V$			± 0.1	μA
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=500V; V_{GS}=0V$			1	μA
V_{SDF}	Diode forward voltage	$I_{SD}=2.9A, V_{GS}=0V$			0.85	V